

Day : Wednesday

Date: 11/8/2006

Time: 14:09:26

PALM INTRANET

**Inventor Name Search Result**

Your Search was:

Last Name = DWILINSKI

First Name = ROBERT

Application#	Patent#	Status	Date Filed	Title	Inventor Name
<u>10479856</u>	<u>7081162</u>	150	06/04/2004	METHOD OF MANUFACTURING BULK SINGLE CRYSTAL OF GALLIUM NITRIDE	DWILINSKI, ROBERT
<del>*10479857</del>	Not Issued	41	06/09/2004	Method for forming gallium-containing nitride bulk single crystal on heterogenous substrate	DWILINSKI, ROBERT
<u>10479858</u>	Not Issued	93	08/31/2004	METHOD AND EQUIPMENT FOR MANUFACTURING ALUMINUM NITRIDE BULK SINGLE CRYSTAL	DWILINSKI, ROBERT
<u>10493594</u>	Not Issued	71	04/26/2004	Light emitting element structure using nitride bulk single crystal layer	DWILINSKI, ROBERT
<u>10493746</u>	<u>7057211</u>	150	04/26/2004	NITRIDE SEMICONDUCTOR LASER DEVICE AND MANUFACTURING METHOD THEREFOR	DWILINSKI, ROBERT
<u>10493747</u>	<u>7132730</u>	150	04/26/2004	BULK NITRIDE MONO-CRYSTAL INCLUDING SUBSTRATE FOR EPITAXY	DWILINSKI, ROBERT
<u>10514429</u>	Not Issued	20	07/12/2005	Phosphor single crystal substrate and method for preparing the same, and nitride semiconductor component using the same	DWILINSKI, ROBERT
<u>10514638</u>	Not Issued	30	08/22/2005	Light emitting device structure having nitride bulk single crystal layer	DWILINSKI, ROBERT
<u>10514639</u>	Not Issued	25	08/30/2005	Bulk single crystal production facility employing supercritical ammonia	DWILINSKI, ROBERT
<u>10519141</u>	Not Issued	30	12/27/2004	Process for obtaining of bulk monocrystalline gallium-	DWILINSKI, ROBERT

				containing nitride	
<a href="#">10519501</a>	Not Issued	41	12/27/2004	Nitride semiconductor laser device and a method for improving its performance	DWILINSKI, ROBERT
<a href="#">10537804</a>	Not Issued	25	06/07/2005	Process for obtaining bulk mono-crystalline gallium-containing nitride	DWILINSKI, ROBERT
<a href="#">10538349</a>	Not Issued	25	06/10/2005	Improved process for obtaining bulk mono-crystalline gallium-containing nitride	DWILINSKI, ROBERT
<a href="#">10538407</a>	Not Issued	20	06/10/2005	Substrate for epitaxy and method of preparing the same	DWILINSKI, ROBERT
<a href="#">10538654</a>	Not Issued	30	06/10/2005	Template type substrate and a method of preparing the same	DWILINSKI, ROBERT
<a href="#">10147318</a>	<a href="#">6656615</a>	150	05/17/2002	BULK MONOCRYSTALLINE GALLIUM NITRIDE	DWILINSKI, ROBERT TOMASZ
<a href="#">10147319</a>	Not Issued	95	05/17/2002	PROCESS AND APPARATUS FOR OBTAINING BULK MONOCRYSTALLINE GALLIUM-CONTAINING NITRIDE	DWILINSKI, ROBERT TOMASZ
<a href="#">10682891</a>	Not Issued	71	10/14/2003	Bulk monocrystalline gallium nitride	DWILINSKI, ROBERT TOMASZ

Inventor Search Completed: No Records to Display.

<b>Search Another: Inventor</b>	<b>Last Name</b>	<b>First Name</b>	<input type="button" value="Search"/>
	<input type="text" value="Dwilinski"/>	<input type="text" value="Robert"/>	

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Day : Wednesday

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**PALM INTRANET****Inventor Name Search Result**

Your Search was:

Last Name = DORADZINSKI

First Name = ROMAN

Application#	Patent#	Status	Date Filed	Title	Inventor Name
<a href="#">10479856</a>	<a href="#">7081162</a>	150	06/04/2004	METHOD OF MANUFACTURING BULK SINGLE CRYSTAL OF GALLIUM NITRIDE	DORADZINSKI, ROMAN
<a href="#">10479857</a>	Not Issued	41	06/09/2004	Method for forming gallium-containing nitride bulk single crystal on heterogenous substrate	DORADZINSKI, ROMAN
<a href="#">10479858</a>	Not Issued	93	08/31/2004	METHOD AND EQUIPMENT FOR MANUFACTURING ALUMINUM NITRIDE BULK SINGLE CRYSTAL	DORADZINSKI, ROMAN
<a href="#">10493594</a>	Not Issued	71	04/26/2004	Light emitting element structure using nitride bulk single crystal layer	DORADZINSKI, ROMAN
<a href="#">10493746</a>	<a href="#">7057211</a>	150	04/26/2004	NITRIDE SEMICONDUCTOR LASER DEVICE AND MANUFACTURING METHOD THEREFOR	DORADZINSKI, ROMAN
<a href="#">10493747</a>	<a href="#">7132730</a>	150	04/26/2004	BULK NITRIDE MONO-CRYSTAL INCLUDING SUBSTRATE FOR EPITAXY	DORADZINSKI, ROMAN
<a href="#">10514429</a>	Not Issued	20	07/12/2005	Phosphor single crystal substrate and method for preparing the same, and nitride semiconductor component using the same	DORADZINSKI, ROMAN
<a href="#">10514638</a>	Not Issued	30	08/22/2005	Light emitting device structure having nitride bulk single crystal layer	DORADZINSKI, ROMAN
<a href="#">10514639</a>	Not Issued	25	08/30/2005	Bulk single crystal production facility employing supercritical ammonia	DORADZINSKI, ROMAN
<a href="#">10519141</a>	Not	30	12/27/2004	Process for obtaining of bulk	DORADZINSKI,

	Issued			monocrystalline gallium-containing nitride	ROMAN
<a href="#">10519501</a>	Not Issued	41	12/27/2004	Nitride semiconductor laser device and a method for improving its performance	DORADZINSKI, ROMAN
<a href="#">10537804</a>	Not Issued	25	06/07/2005	Process for obtaining bulk mono-crystalline gallium-containing nitride	DORADZINSKI, ROMAN
<a href="#">10538349</a>	Not Issued	25	06/10/2005	Improved process for obtaining bulk mono-crystalline gallium-containing nitride	DORADZINSKI, ROMAN
<a href="#">10538407</a>	Not Issued	20	06/10/2005	Substrate for epitaxy and method of preparing the same	DORADZINSKI, ROMAN
<a href="#">10538654</a>	Not Issued	30	06/10/2005	Template type substrate and a method of preparing the same	DORADZINSKI, ROMAN
<a href="#">10147318</a>	<a href="#">6656615</a>	150	05/17/2002	BULK MONOCRYSTALLINE GALLIUM NITRIDE	DORADZINSKI, ROMAN MAREK
<a href="#">10147319</a>	Not Issued	95	05/17/2002	PROCESS AND APPARATUS FOR OBTAINING BULK MONOCRYSTALLINE GALLIUM-CONTAINING NITRIDE	DORADZINSKI, ROMAN MAREK
<a href="#">10479807</a>	Not Issued	100	12/05/2003	PROCESS AND APPARATUS FOR OBTAINING BULK MONOCRYSTALLINE GALLIUM-CONTAINING NITRIDE	DORADZINSKI, ROMAN MAREK
<a href="#">10682891</a>	Not Issued	71	10/14/2003	Bulk monocrystalline gallium nitride	DORADZINSKI, ROMAN MAREK

Inventor Search Completed: No Records to Display.

<b>Search Another: Inventor</b>	<b>Last Name</b>	<b>First Name</b>	<input type="button" value="Search"/>
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Day : Wednesday

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**PALM INTRANET****Inventor Name Search Result**

Your Search was:

Last Name = GARCZYNSKI

First Name = JERZY

Application#	Patent#	Status	Date Filed	Title	Inventor Name
<a href="#">10147318</a>	6656615	150	05/17/2002	BULK MONOCRYSTALLINE GALLIUM NITRIDE	GARCZYNSKI, JERZY
<a href="#">10147319</a>	Not Issued	95	05/17/2002	PROCESS AND APPARATUS FOR OBTAINING BULK MONOCRYSTALLINE GALLIUM-CONTAINING NITRIDE	GARCZYNSKI, JERZY
<a href="#">10479807</a>	Not Issued	100	12/05/2003	PROCESS AND APPARATUS FOR OBTAINING BULK MONOCRYSTALLINE GALLIUM-CONTAINING NITRIDE	GARCZYNSKI, JERZY
<a href="#">10479856</a>	7081162	150	06/04/2004	METHOD OF MANUFACTURING BULK SINGLE CRYSTAL OF GALLIUM NITRIDE	GARCZYNSKI, JERZY
<a href="#">10479857</a>	Not Issued	41	06/09/2004	Method for forming gallium-containing nitride bulk single crystal on heterogenous substrate	GARCZYNSKI, JERZY
<a href="#">10479858</a>	Not Issued	93	08/31/2004	METHOD AND EQUIPMENT FOR MANUFACTURING ALUMINUM NITRIDE BULK SINGLE CRYSTAL	GARCZYNSKI, JERZY
<a href="#">10493594</a>	Not Issued	71	04/26/2004	Light emitting element structure using nitride bulk single crystal layer	GARCZYNSKI, JERZY
<a href="#">10493746</a>	7057211	150	04/26/2004	NITRIDE SEMICONDUCTOR LASER DEVICE AND MANUFACTURING METHOD THEREFOR	GARCZYNSKI, JERZY
<a href="#">10493747</a>	7132730	150	04/26/2004	BULK NITRIDE MONO-CRYSTAL INCLUDING SUBSTRATE FOR EPITAXY	GARCZYNSKI, JERZY

<a href="#">10514429</a>	Not Issued	20	07/12/2005	Phosphor single crystal substrate and method for preparing the same, and nitride semiconductor component using the same	GARCZYNSKI, JERZY
<a href="#">10514638</a>	Not Issued	30	08/22/2005	Light emitting device structure having nitride bulk single crystal layer	GARCZYNSKI, JERZY
<a href="#">10514639</a>	Not Issued	25	08/30/2005	Bulk single crystal production facility employing supercritical ammonia	GARCZYNSKI, JERZY
<a href="#">10519141</a>	Not Issued	30	12/27/2004	Process for obtaining of bulk monocrystalline gallium-containing nitride	GARCZYNSKI, JERZY
<a href="#">10519501</a>	Not Issued	41	12/27/2004	Nitride semiconductor laser device and a method for improving its performance	GARCZYNSKI, JERZY
<a href="#">10537804</a>	Not Issued	25	06/07/2005	Process for obtaining bulk monocrystalline gallium-containing nitride	GARCZYNSKI, JERZY
<a href="#">10538349</a>	Not Issued	25	06/10/2005	Improved process for obtaining bulk mono-crystalline gallium-containing nitride	GARCZYNSKI, JERZY
<a href="#">10538407</a>	Not Issued	20	06/10/2005	Substrate for epitaxy and method of preparing the same	GARCZYNSKI, JERZY
<a href="#">10538654</a>	Not Issued	30	06/10/2005	Template type substrate and a method of preparing the same	GARCZYNSKI, JERZY
<a href="#">10682891</a>	Not Issued	71	10/14/2003	Bulk monocrystalline gallium nitride	GARCZYNSKI, JERZY

**Inventor Search Completed:** No Records to Display.

**Search Another: Inventor**

<b>Last Name</b>	<b>First Name</b>	
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Day : Wednesday

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 **PALM INTRANET****Inventor Name Search Result**

Your Search was:

Last Name = SIERPUTOWSKI

First Name = LESZEK

Application#	Patent#	Status	Date Filed	Title	Inventor Name
<u>10519141</u>	Not Issued	30	12/27/2004	Process for obtaining of bulk monocrystalline gallium- containing nitride	SIERPUTOWSKI, LESZEK P.

**Inventor Search Completed: No Records to Display.**

<b>Search Another: Inventor</b>	<b>Last Name</b>	<b>First Name</b>	<input type="button" value="Search"/>
	<input type="text" value="Sierputowski"/>	<input type="text" value="Leszek"/>	

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PALM INTRANET

**Inventor Name Search Result**

Your Search was:

Last Name = KANBARA

First Name = YASUO

Application#	Patent#	Status	Date Filed	Title	Inventor Name
<a href="#">10147318</a>	<a href="#">6656615</a>	150	05/17/2002	BULK MONOCRYSTALLINE GALLIUM NITRIDE	KANBARA, YASUO
<a href="#">10147319</a>	Not Issued	95	05/17/2002	PROCESS AND APPARATUS FOR OBTAINING BULK MONOCRYSTALLINE GALLIUM-CONTAINING NITRIDE	KANBARA, YASUO
<a href="#">10192246</a>	<a href="#">7042830</a>	150	07/09/2002	PHASE-CHANGE OPTICAL INFORMATION RECORDING MEDIUM, AND OPTICAL INFORMATION RECORDING AND REPRODUCING APPARATUS AND METHOD FOR THE SAME	KANBARA, YASUO
<a href="#">10479807</a>	Not Issued	100	12/05/2003	PROCESS AND APPARATUS FOR OBTAINING BULK MONOCRYSTALLINE GALLIUM-CONTAINING NITRIDE	KANBARA, YASUO
<a href="#">10479856</a>	<a href="#">7081162</a>	150	06/04/2004	METHOD OF MANUFACTURING BULK SINGLE CRYSTAL OF GALLIUM NITRIDE	KANBARA, YASUO
<a href="#">10479857</a>	Not Issued	41	06/09/2004	Method for forming gallium-containing nitride bulk single crystal on heterogenous substrate	KANBARA, YASUO
<a href="#">10479858</a>	Not Issued	93	08/31/2004	METHOD AND EQUIPMENT FOR MANUFACTURING ALUMINUM NITRIDE BULK SINGLE CRYSTAL	KANBARA, YASUO
<a href="#">10493594</a>	Not Issued	71	04/26/2004	Light emitting element structure using nitride bulk single crystal layer	KANBARA, YASUO
<a href="#">10493746</a>	<a href="#">7057211</a>	150	04/26/2004	NITRIDE SEMICONDUCTOR	KANBARA,



				LASER DEVICE AND MANUFACTURING METHOD THEREFOR	YASUO
<u>10493747</u>	<u>7132730</u>	150	04/26/2004	BULK NITRIDE MONO- CRYSTAL INCLUDING SUBSTRATE FOR EPITAXY	KANBARA, YASUO
<u>10514429</u>	Not Issued	20	07/12/2005	Phosphor single crystal substrate and method for preparing the same, and nitride semiconductor component using the same	KANBARA, YASUO
<u>10514638</u>	Not Issued	30	08/22/2005	Light emitting device structure having nitride bulk single crystal layer	KANBARA, YASUO
<u>10514639</u>	Not Issued	25	08/30/2005	Bulk single crystal production facility employing supercritical ammonia	KANBARA, YASUO
<u>10519141</u>	Not Issued	30	12/27/2004	Process for obtaining of bulk monocrystalline gallium- containing nitride	KANBARA, YASUO
<u>10519501</u>	Not Issued	41	12/27/2004	Nitride semiconductor laser device and a method for improving its performance	KANBARA, YASUO
<u>10537804</u>	Not Issued	25	06/07/2005	Process for obtaining bulk mono- crystalline gallium-containing nitride	KANBARA, YASUO
<u>10538349</u>	Not Issued	25	06/10/2005	Improved process for obtaining bulk mono-crystalline gallium- containing nitride	KANBARA, YASUO
<u>10538407</u>	Not Issued	20	06/10/2005	Substrate for epitaxy and method of preparing the same	KANBARA, YASUO
<u>10538654</u>	Not Issued	30	06/10/2005	Template type substrate and a method of preparing the same	KANBARA, YASUO
<u>10682891</u>	Not Issued	71	10/14/2003	Bulk monocrystalline gallium nitride	KANBARA, YASUO

Inventor Search Completed: No Records to Display.

<b>Search Another: Inventor</b>	<b>Last Name</b>	<b>First Name</b>	<input type="button" value="Search"/>
	<input type="text" value="Kanbara"/>	<input type="text" value="Yasuo"/>	

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